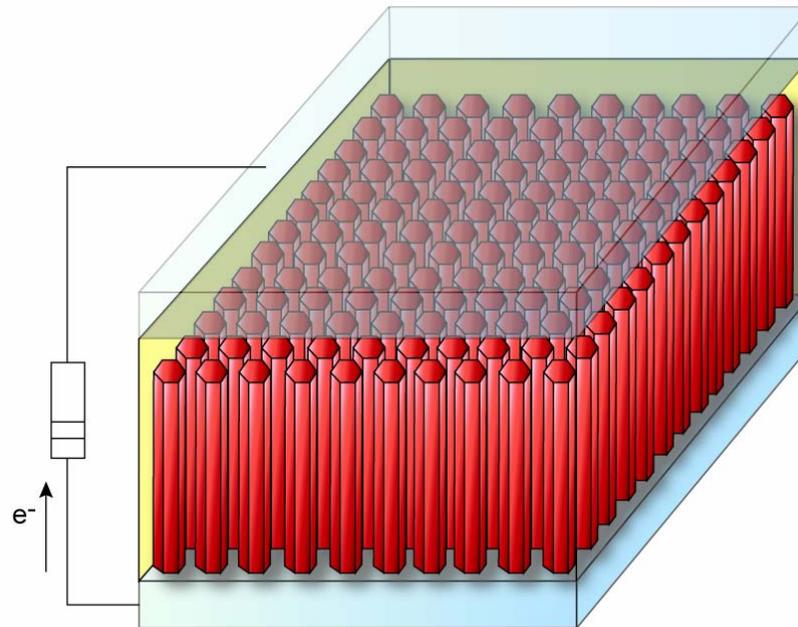


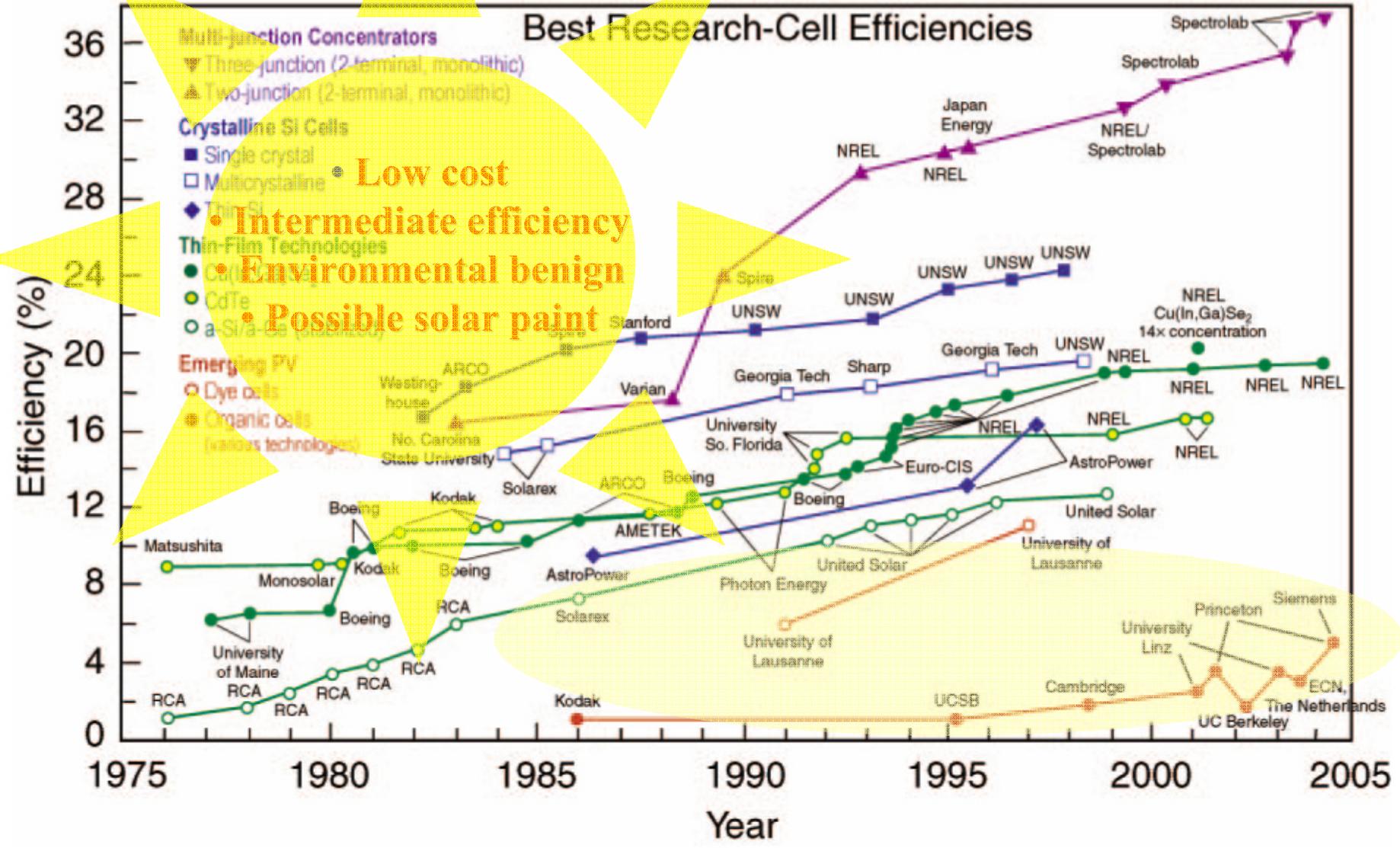
# Nanowire Solar Cells



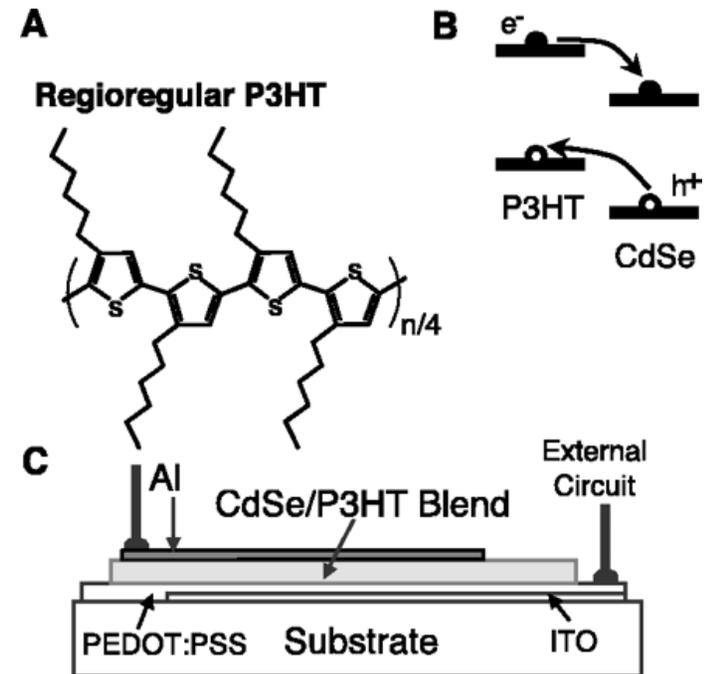
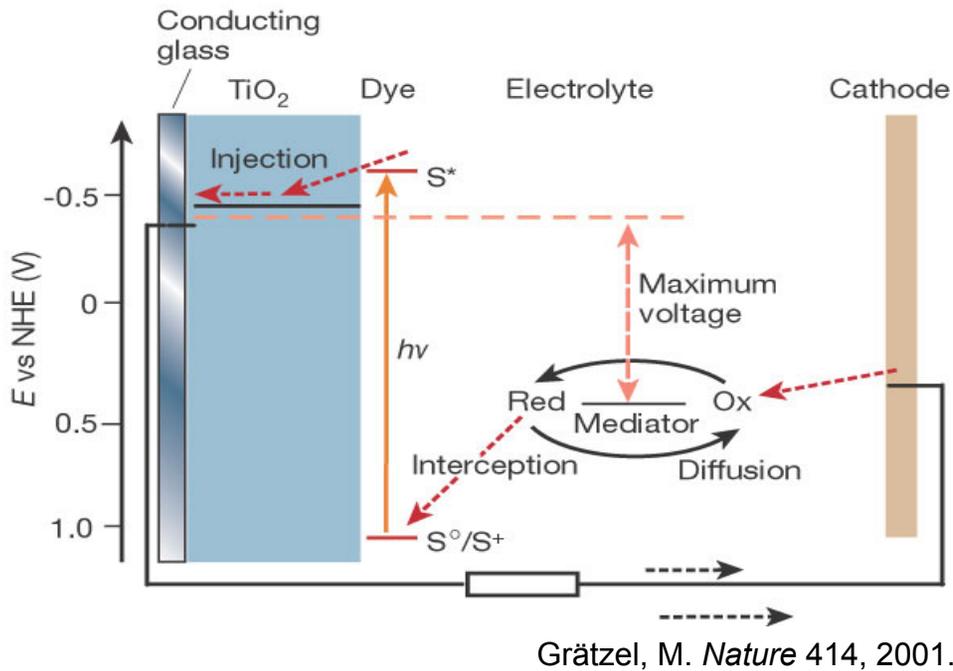
Peidong Yang  
Department of Chemistry  
University of California, Berkeley  
Materials Science Division  
Lawrence Berkeley National Laboratory

**Materials Sciences Division**

# Emerging PV

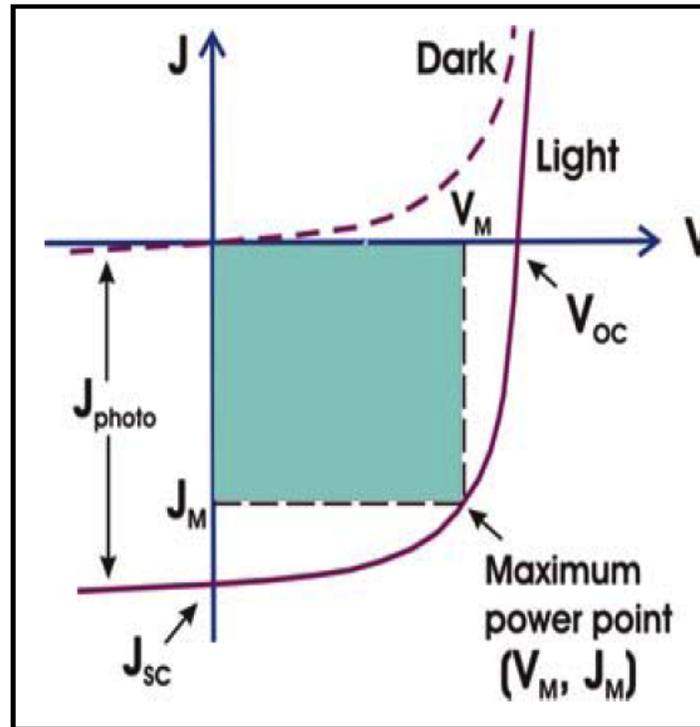


# Emerging PV



## Why nanowires are important?

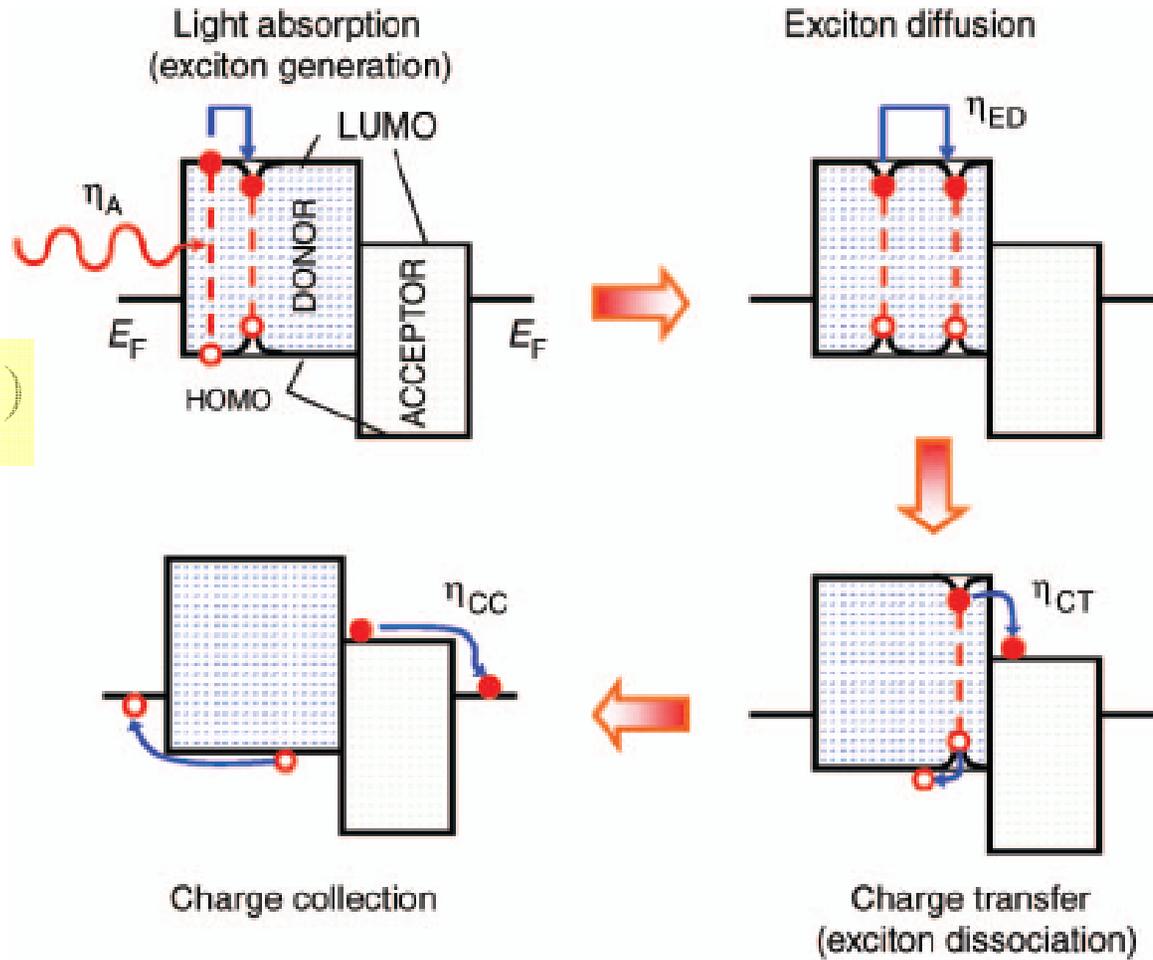
# PV Performance Metrics



$$FF = \frac{J_M V_M}{J_{sc} V_{oc}}$$

$$\text{Efficiency} = \frac{P_{out}}{P_{in}} = \frac{FF \times V_{oc} \times J_{sc}}{P_{in}}$$

$$\eta_A = (1 - e^{-\alpha d})$$



$$\eta_{ED} = e^{-d/L_D}$$

$$IQE(\lambda) = \eta_A(\lambda) \eta_{ED} \eta_{CT} \eta_{CC}$$

$$\eta_{PCE} = \frac{P_{out}}{P_{in}} = \frac{FF \times V_{oc}}{P_{in}} q \int F(\lambda) IQE(\lambda) d\lambda$$

# Emerging PV



- Use of solar at terawatt levels requires drop in  $\$/W_p$

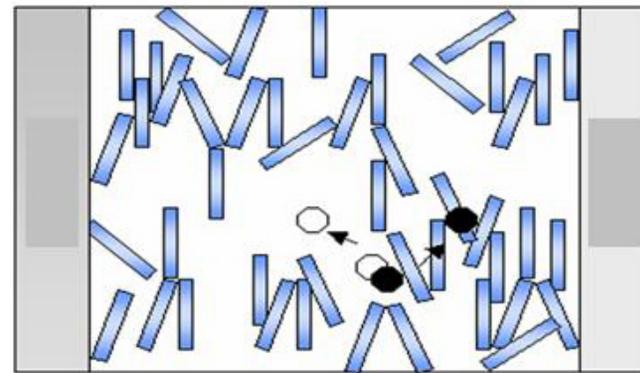
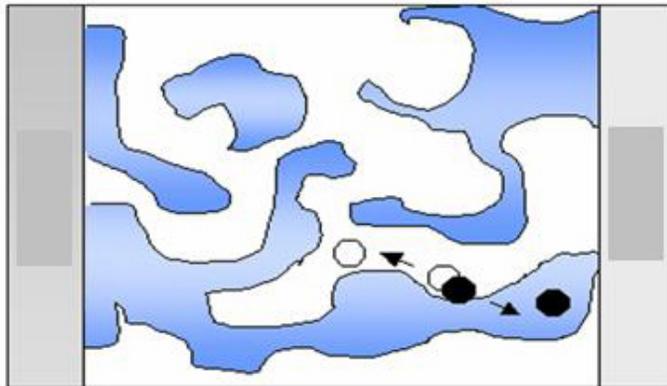
- 3N:** New materials, New designs, New tricks

“dirty” semiconductors  
organics  
oxides  
absorbers  
biological subunits

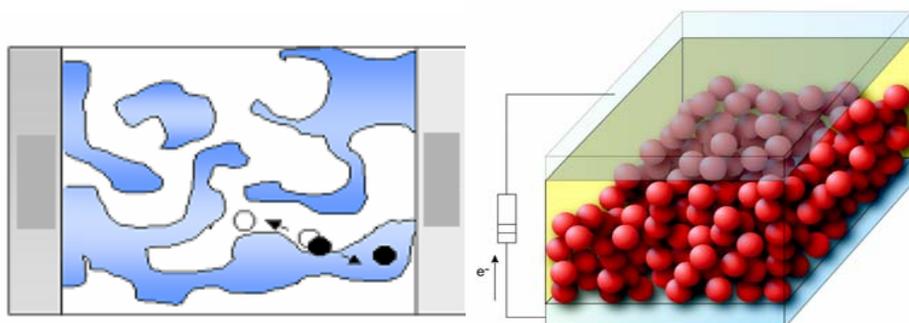
dye-sensitized cells

bulk heterojunction cells  
(polymer, organic-inorganic)

quantum effects  
carrier multiplication  
frequency shifting  
Interface engineering

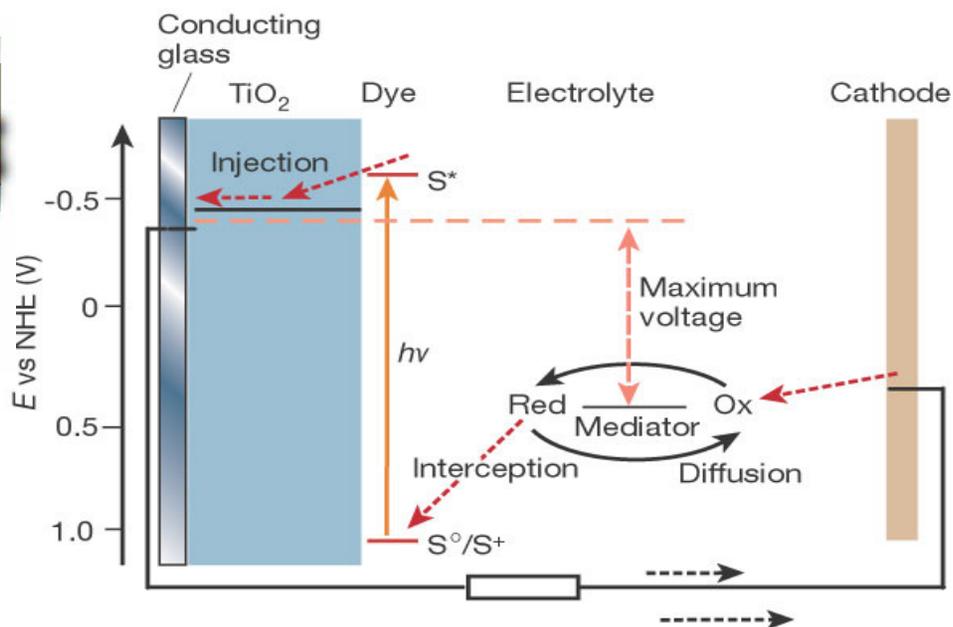


# Dye-sensitized Photoelectrochemical Cell

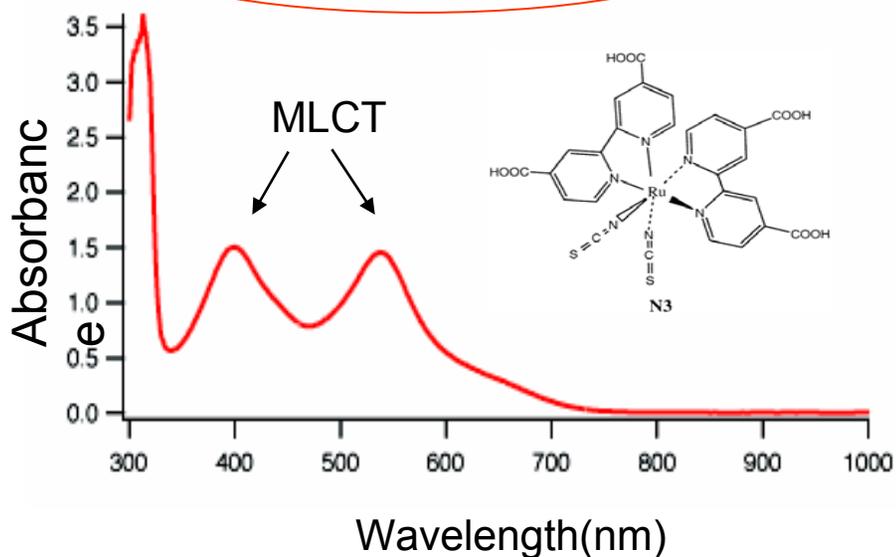


electron diffusivity:  $10^{-4} \text{ cm}^2/\text{s}$

Poor charge collectors?



Grätzel, M. *Nature* 414, 2001.



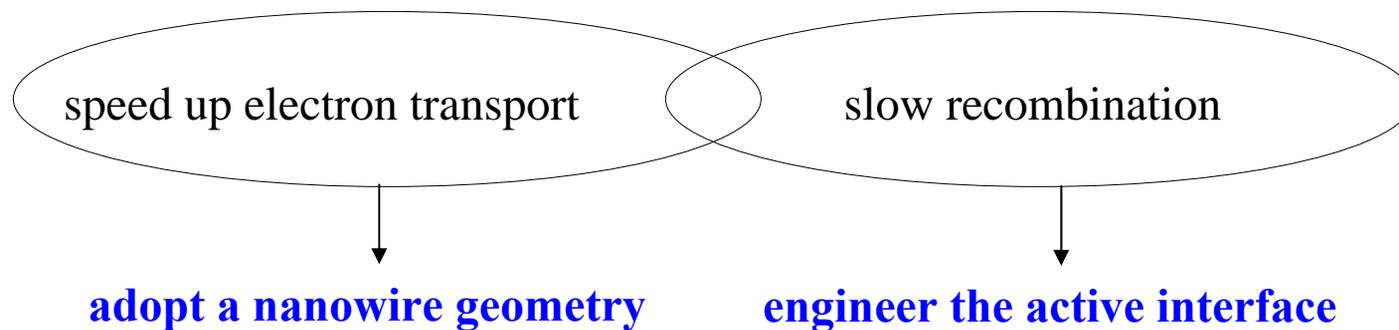
## DSC characteristics

- surface area of 800 – 1000  $\text{cm}^2$  per  $\text{cm}^2$
- $\eta$  of 5 -10% with  $\text{TiO}_2$  nanoparticles
- electron transport via trap-mediated diffusior
- Low efficiency at long wavelength

# The three ways to improve DSC efficiency

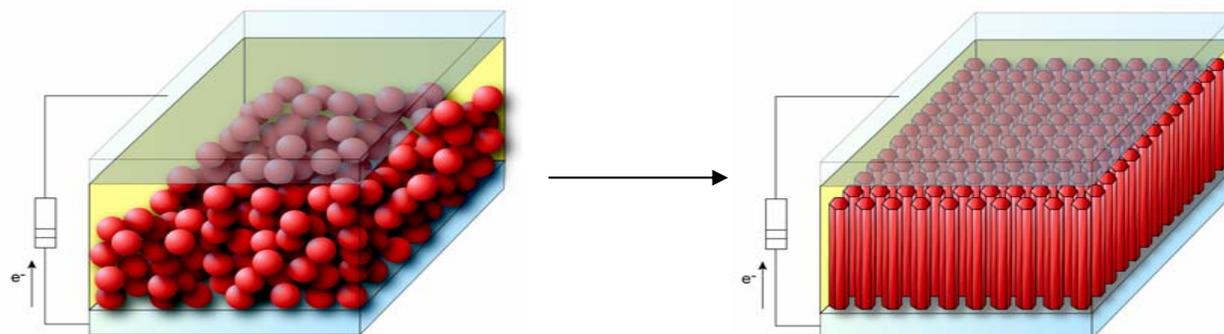


- 1) Find dyes that function efficiently across the visible and near-IR
- 2) Raise open-circuit voltage closer to its theoretical maximum
- 3) Increase the electron diffusion length in the oxide anode,  $L_d = (D_e \tau)^{1/2}$



Nanoparticle DSC	Nanowire DSC
random, polycrystalline network	oriented single-crystalline channels
slow diffusive transport	fast band conduction (field-assisted)
efficient for films ~10 $\mu\text{m}$ thick	in principle, efficient for much thicker cells
<i>high internal surface area</i>	<i>smaller internal surface area</i>

# Nanowire DSC: Design Principle



high nanowire density  
long, thin nanowires

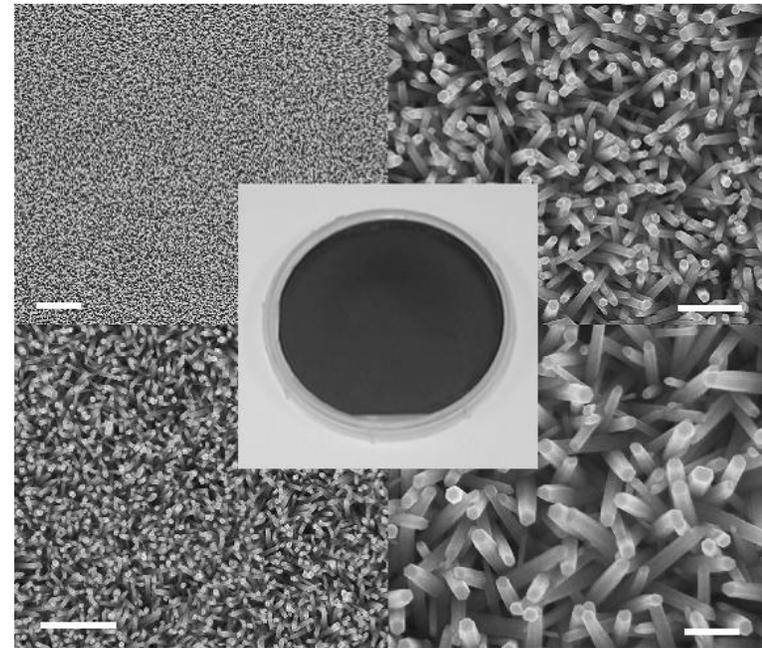
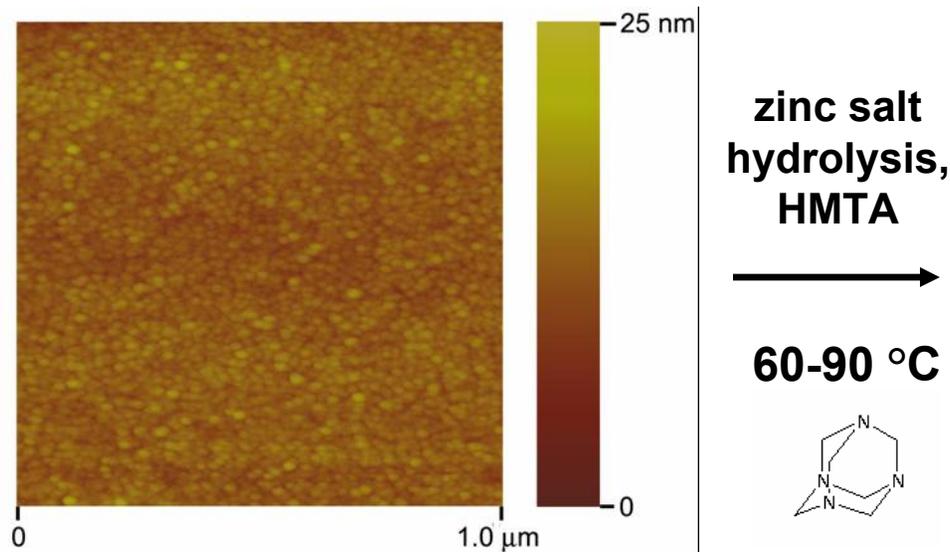
electrode	length ( $\mu\text{m}$ )	diameter (nm)	density ( $\times 10^{10} \text{ cm}^{-2}$ )	SA
nanoparticle	8 - 10	15 - 30	n/a	800 - 1000
<b>ideal nanowire</b>	<b>20</b>	<b>60</b>	<b>3</b>	<b>1080</b>
achieved NW	20	130	0.3	~200

# Large-Scale Nanowire Array Synthesis



1<sup>st</sup>: dip-coat to get ZnO quantum dots

2<sup>nd</sup>: grow nanowires from QD seeds



*L. Greene et al. Angew Chem. Int. Ed. 42, 3031, 2003.*

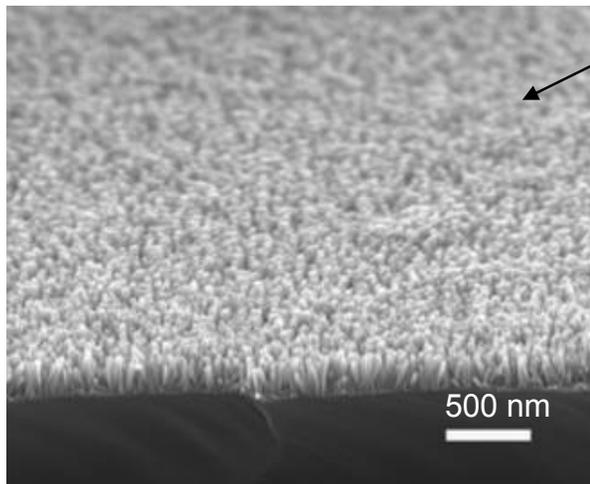
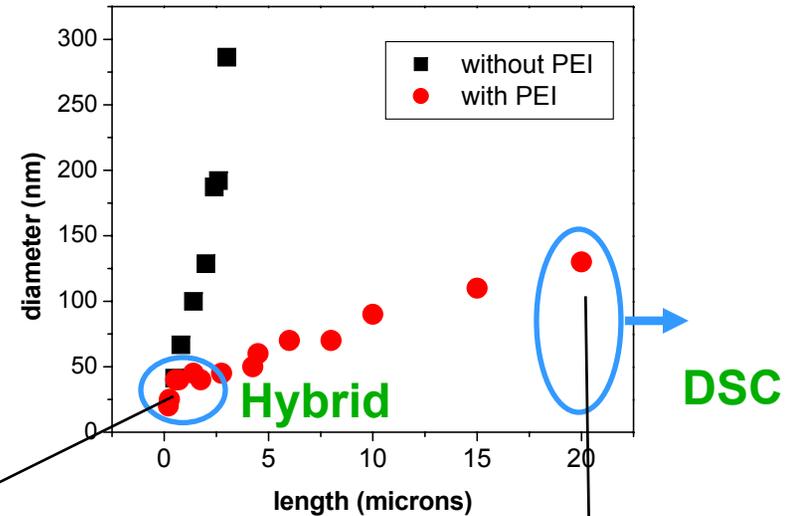
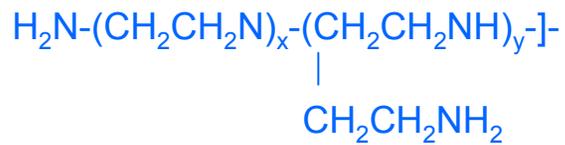
- Nanowire densities of 1-40 billion  $\text{cm}^{-2}$
- Single-crystalline wires in direct contact with the substrate
- Inexpensive and environmentally benign
- Compatible with arbitrary substrates of any size



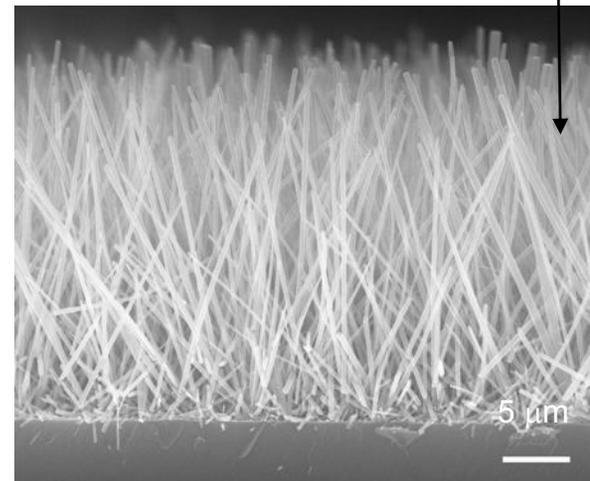
# Control of Nanowire Aspect Ratio



**Poly-ethylenimine (PEI):**

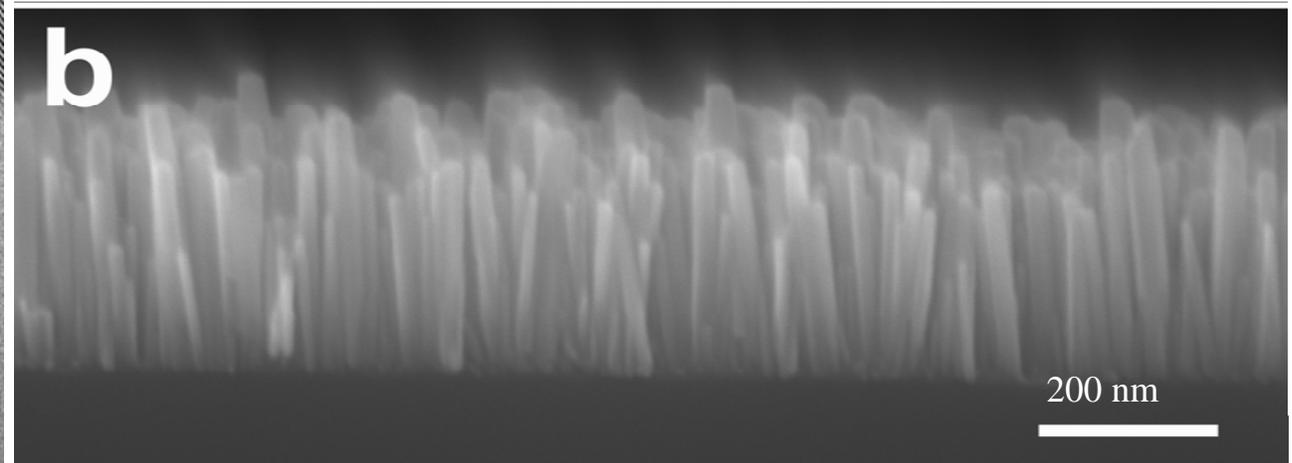
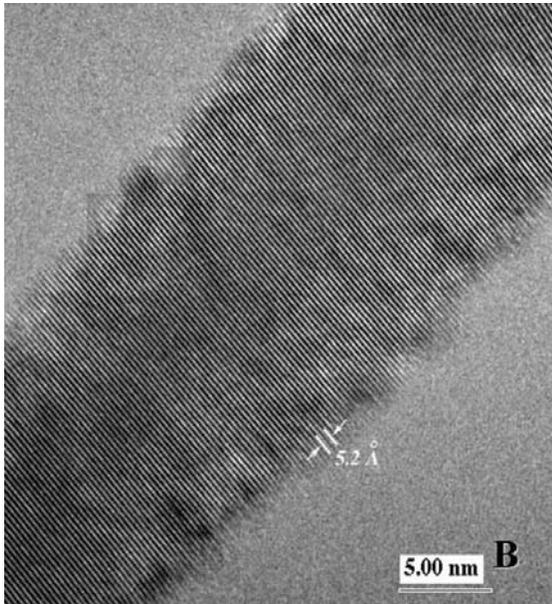
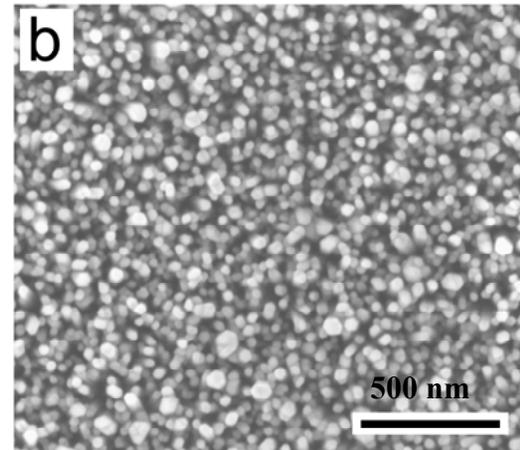
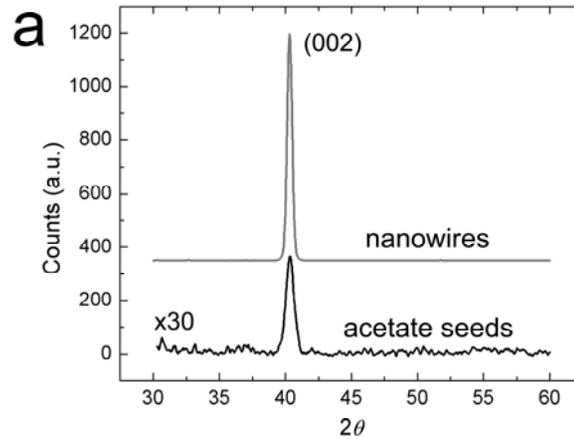


**Hybrid: aspect ratio = 10**



**DSC: aspect ratio > 150**

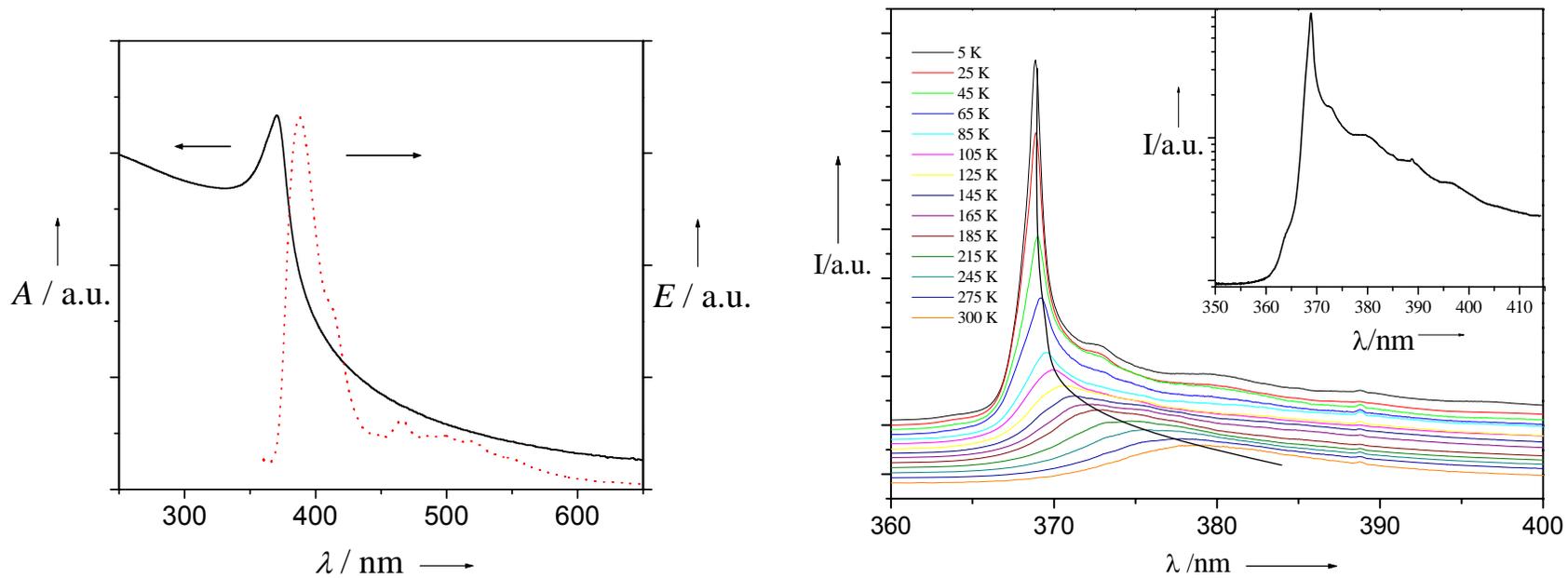
# Alignment Control



Greene, L.E., Law, M. et al. *Nano Letters* **5**, 1231 (2005).

**Materials Sciences Division**

# High Optical Quality

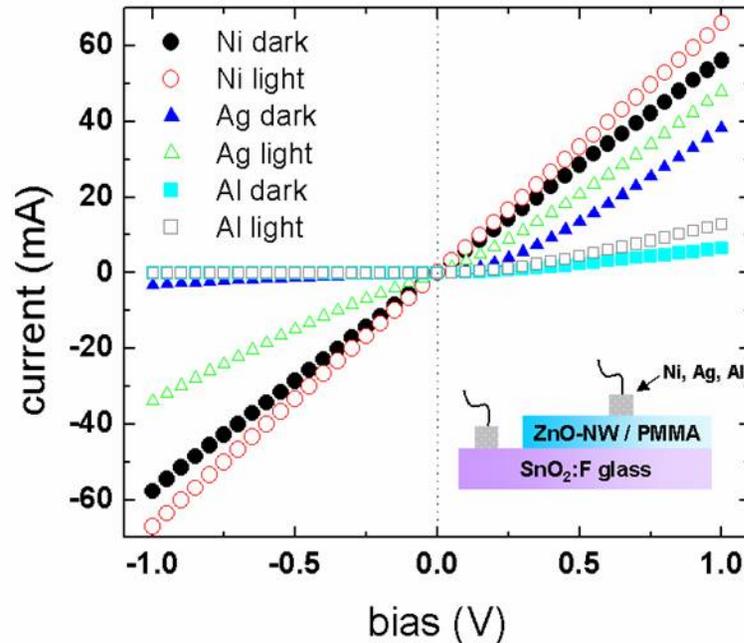


- TEM shows that the nanowires are single crystals
- Wire surfaces are clean (Raman, EELS) after 400 °C treatment

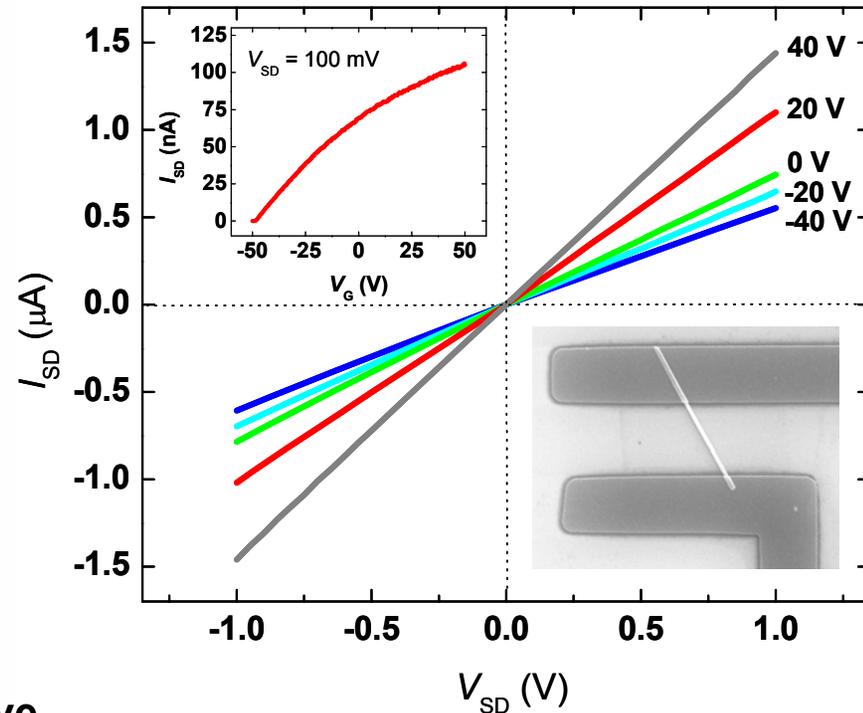
# Characterization of Nanowire Arrays



## Electrical: Ohmic wire-substrate contacts



## FETs: Wires have high e<sup>-</sup> mobility



- Individual wires are electrically conductive

$$\rho = 0.1 - 1 \Omega \text{ cm}$$

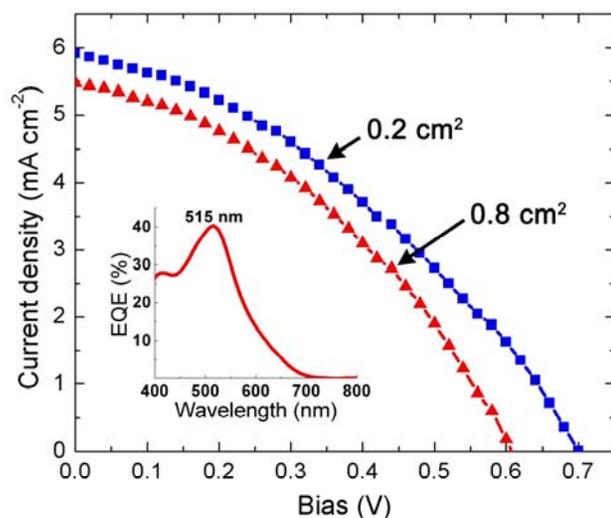
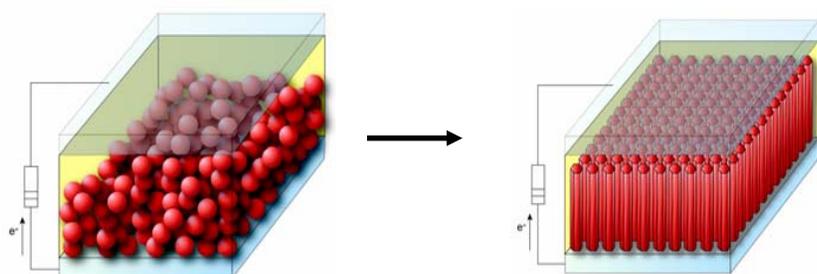
$$\text{mobility: } 1\text{-}5 \text{ cm}^2\text{V}^{-1}\text{s}^{-1}$$

$$\text{electron diffusivity: } D_n = 0.05\text{-}0.5 \text{ cm}^2\text{s}^{-1} [D = k_B T \mu / e]$$

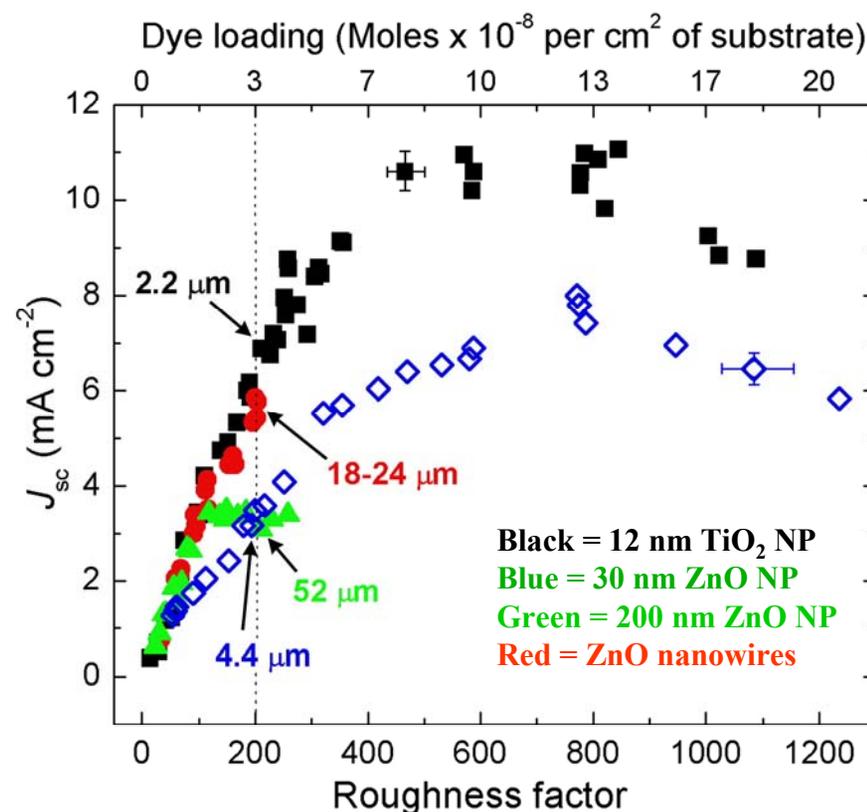
Ensure larger electron diffusion length, avoiding possible interfacial recombination

Law, M., Greene, L. et al.  
*Nature Mater.* **4**, 455 (2005).

# Nanowire based DSC



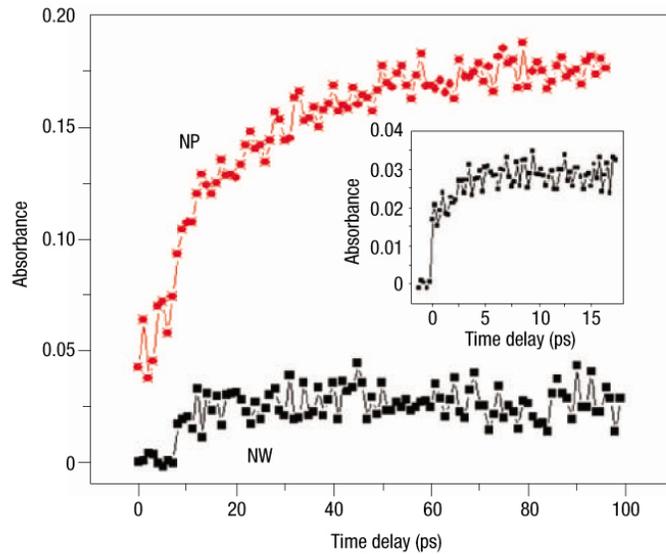
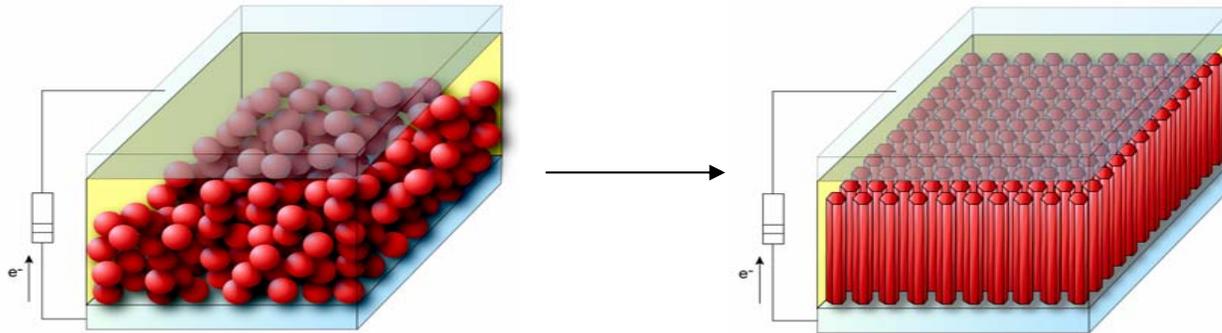
$\eta_{\text{PCE}} = 1.5\%$  under AM  
1.5 G conditions



- NW cells are competitive with thin  $\text{TiO}_2$  nanoparticle cells ( $\eta_{\text{cc}} \sim 100\%$ )
- NW cells outperform ZnO nanoparticle cells

Law, M., Greene, L. et al. *Nature Mater.* **4**, 455 (2005).

# Nanowire DSC



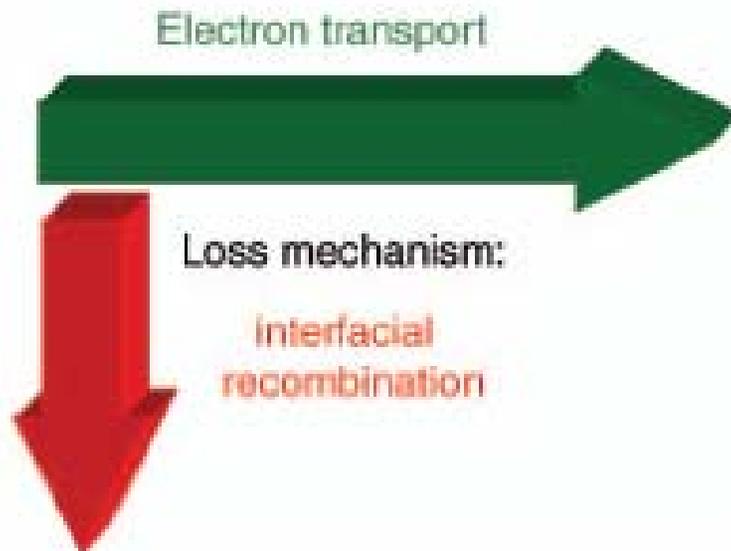
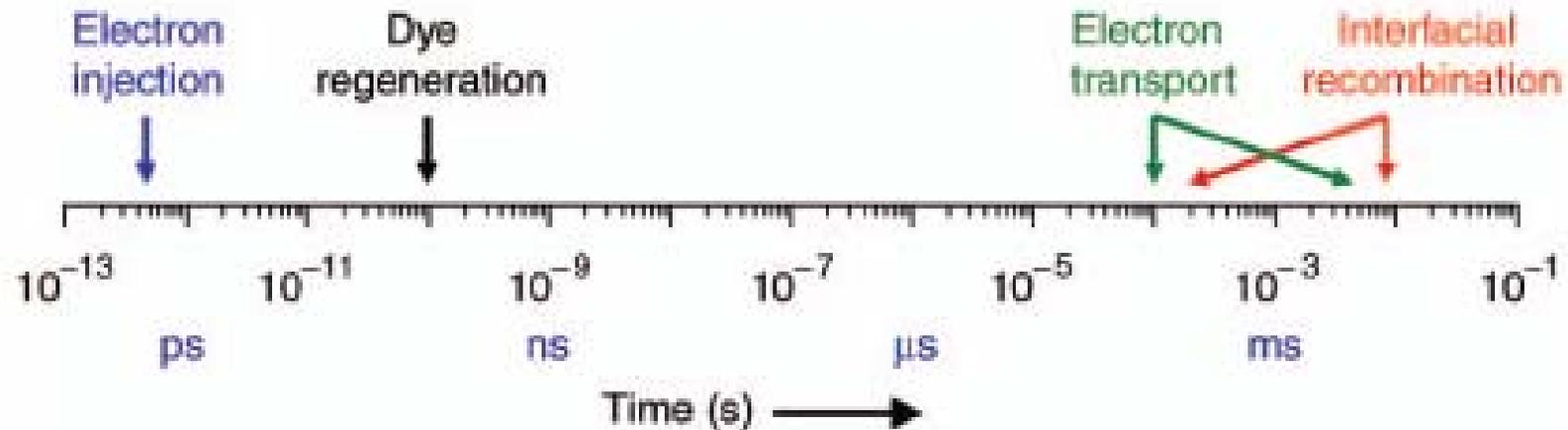
**Faster electron injection in NW cell**

Bi-exponential (<250fs, 3ps)

VS.

Tri-exponential (<250fs, 20ps, 200ps)

# Time Scale for Electron Injection and Transport



Competition ⇒

Electron diffusion length

$$L_n = \sqrt{D_n \cdot \tau_n}$$

$D_n$ : electron diffusion coefficient

$\tau_n$ : electron lifetime

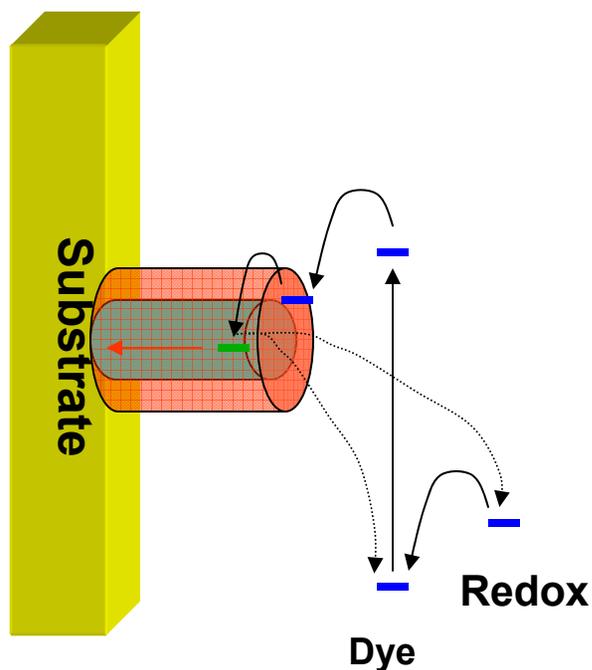
Grätzel, M, MRS Bulletin, Jan 2005

# Engineer active interface to reduce recombination



## Core-sheath Nanowire Cells

Overcoat the nanostructured electrode with an insulating or semiconducting oxide



### Reduce recombination

- Physically separate electrons and holes
- Form a tunneling barrier
- Passivate recombination centers on oxide surface

### Shift band edge to increase $V_{oc}$

- Use an oxide with a higher band edge energy
- Form dipole layer that bends band upwards

TABLE 1: Bulk Characteristics of the Metal Oxides Used in This Study

metal oxide	band gap (eV)	$E_{VB}$ (eV vs AVS) <sup>a</sup>	$E_{CB}$ (eV vs AVS) <sup>a</sup>	Pzc (pH) <sup>b</sup>
ZnO	3.2	-7.4	-4.19	8.5-9.5
TiO <sub>2</sub> (anatase)	3.2	-7.4	-4.21	5.5-6.5
Al <sub>2</sub> O <sub>3</sub>	8.0-9.5	-9.9	-1.6	8.5-9.5

<sup>a</sup> AVS = Absolute Vacuum Scale. From references 18-20. <sup>b</sup> The point of zero charge (Pzc) depends on sample preparation, impurities, etc. From references 21 - 23.

Gregg, B. NREL.

# Atomic Layer Deposition (ALD)

**Oxides:**  $\text{Al}_2\text{O}_3$ ,  $\text{TiO}_2$ ,  $\text{Ta}_2\text{O}_5$ ,  $\text{Nb}_2\text{O}_5$ ,  $\text{ZrO}_2$ ,  $\text{HfO}_2$ ,  $\text{SnO}_2$ ,  $\text{ZnO}$ ,  $\text{La}_2\text{O}_3$ ,  $\text{Y}_2\text{O}_3$ ,  $\text{CeO}_2$ ,  $\text{Sc}_2\text{O}_3$ ,  $\text{Er}_2\text{O}_3$ ,  $\text{V}_2\text{O}_5$ ,  $\text{SiO}_2$ ,  $\text{In}_2\text{O}_3$ , ...

**Perovskites:**  $\text{SrTiO}_3$ ,  $\text{BaTiO}_3$ ,  $\text{LiNbO}_3$ ,  $\text{LaMnO}_3$  ...

**Nitrides:**  $\text{AlN}$ ,  $\text{Ta}_x\text{N}$ ,  $\text{NbN}$ ,  $\text{TiN}$ ,  $\text{MoN}$ ,  $\text{ZrN}$ ,  $\text{HfN}$ ,  $\text{GaN}$ , ... **Fluorides:**  $\text{CaF}_2$ ,  $\text{SrF}_2$ ,  $\text{ZnF}_2$ , ...

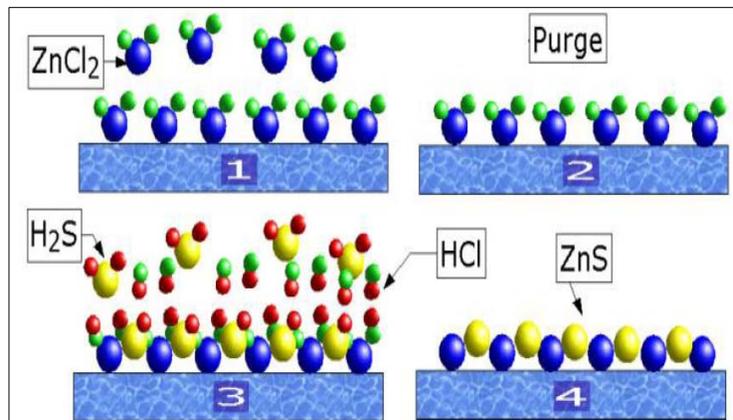
**Metals:** Pt, Ru, Ir, Pd, Cu, Fe, Co, Ni, ... **Carbides:**  $\text{TiC}$ ,  $\text{NbC}$ ,  $\text{TaC}$ , ...

**Mixed structures:**  $\text{AlTiN}_x$ ,  $\text{AlTiO}_x$ ,  $\text{AlHfO}_x$ ,  $\text{SiO}_2:\text{Al}$ ,  $\text{HfSiO}_x$ , ... **Sulfides:**  $\text{ZnS}$ ,  $\text{SrS}$ ,  $\text{CaS}$ ,  $\text{PbS}$ , ...

**Nanolaminates:**  $\text{HfO}_2/\text{Ta}_2\text{O}_5$ ,  $\text{TiO}_2/\text{Ta}_2\text{O}_5$ ,  $\text{TiO}_2/\text{Al}_2\text{O}_3$ ,  $\text{ZnS}/\text{Al}_2\text{O}_3$ ,  $\text{ATO}$  ( $\text{AlTiO}$ ) ...

**Doping:**  $\text{ZnO}:\text{Al}$ ,  $\text{ZnS}:\text{Mn}$ ,  $\text{SrS}:\text{Ce}$ ,  $\text{Al}_2\text{O}_3:\text{Er}$ ,  $\text{ZrO}_2:\text{Y}$ , ... rare earth metals ( $\text{Ce}^{3+}$ ,  $\text{Tb}^{3+}$  etc.) also co-doping

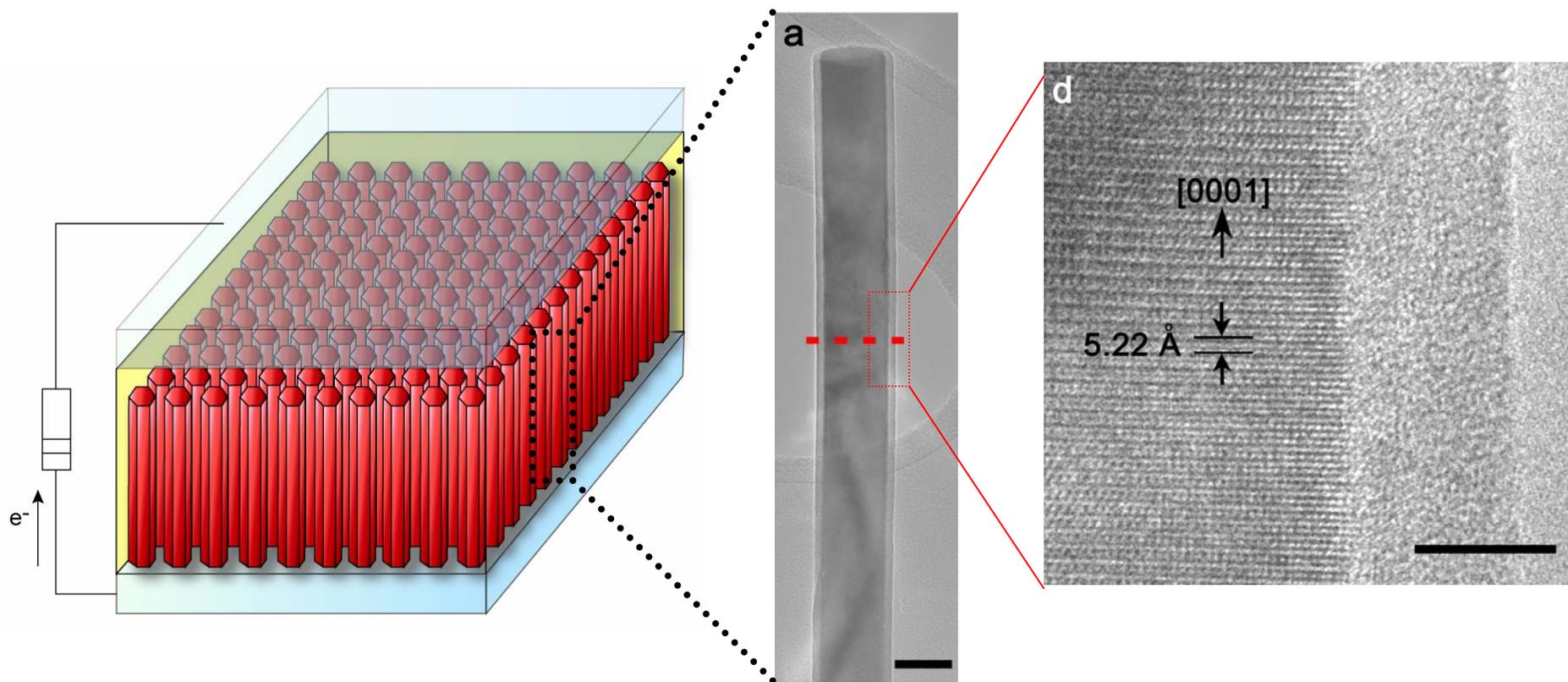
Example: ZnS



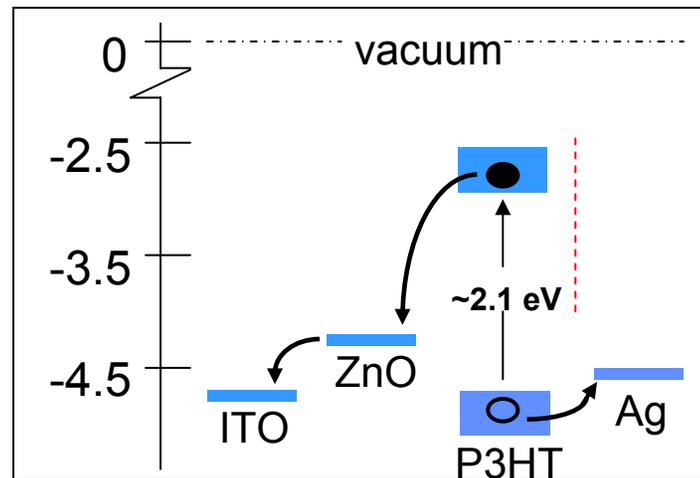
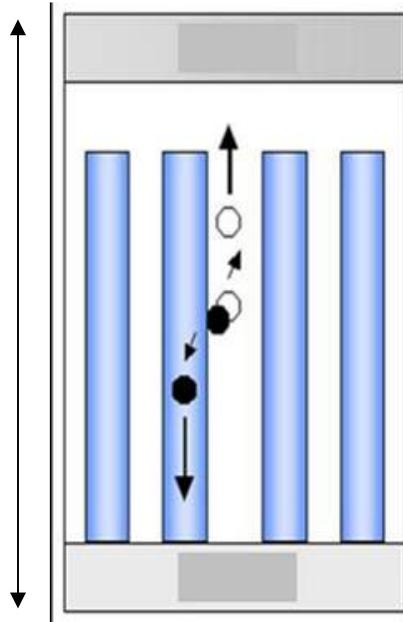
Planar Systems, Inc.



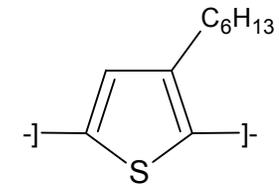
# Core-sheath Nanowire Dye-sensitized Solar Cells



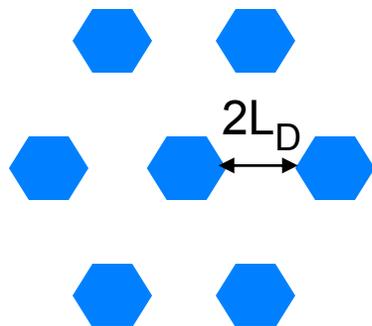
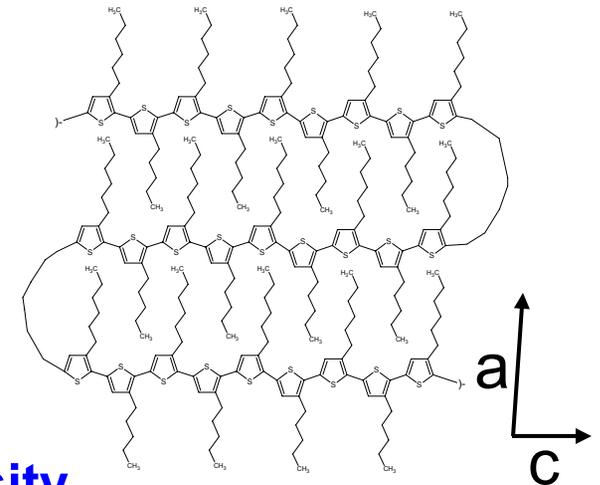
# Nanowire-polymer Hybrid Cell



## Poly(3-hexylthiophene)



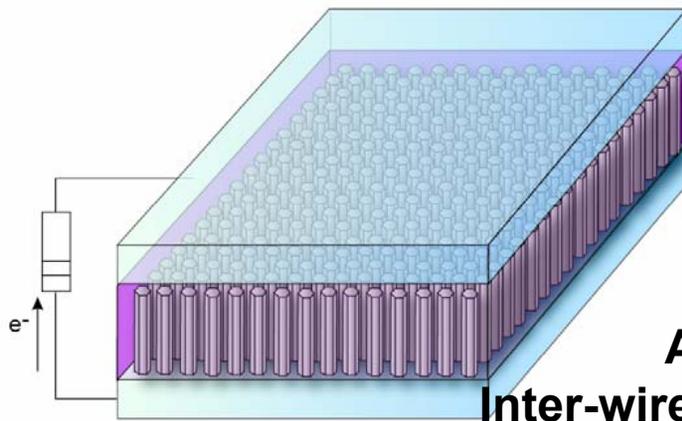
$2L_D \sim 20 \text{ nm}$



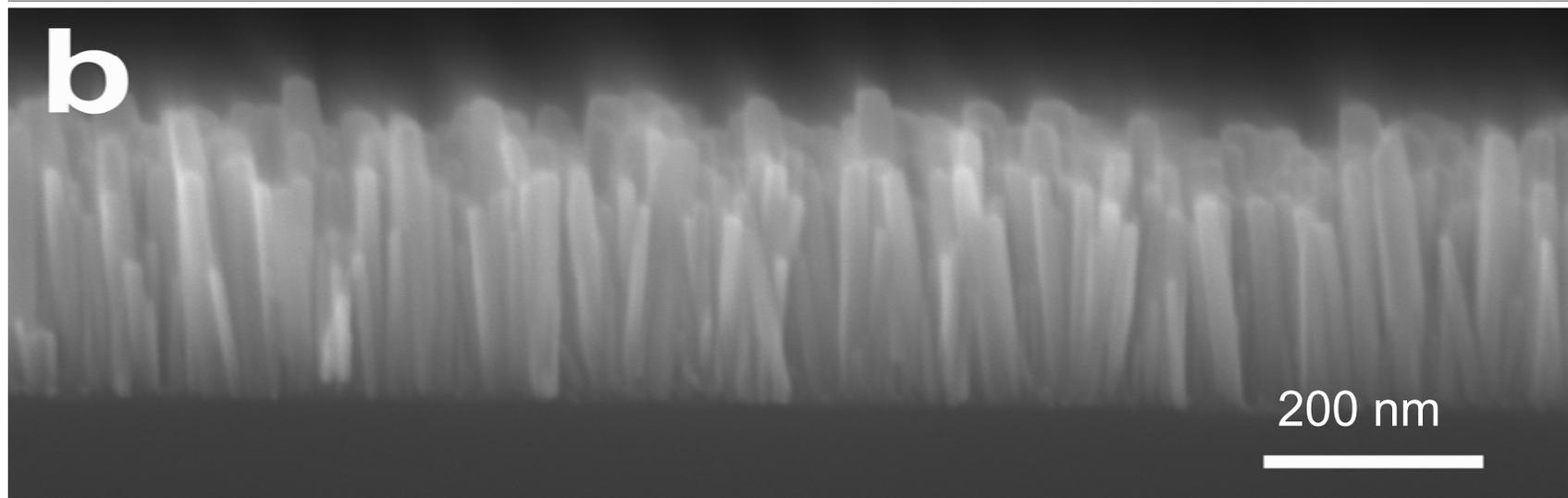
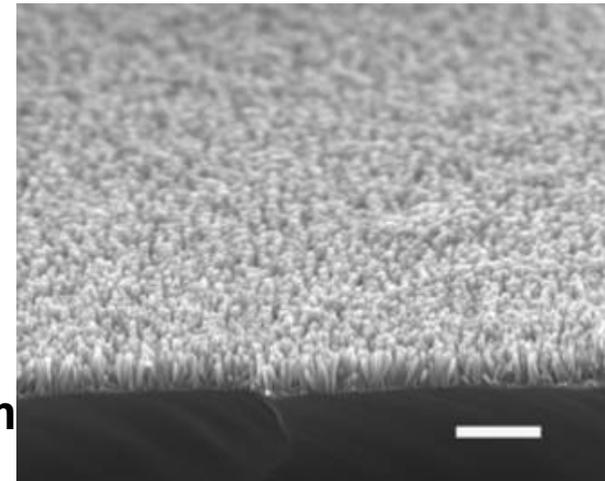
## Target nanowire array

- 1) ultrahigh nanowire density
- 2) short, thin nanowires
- 3) nanowires normal to substrate

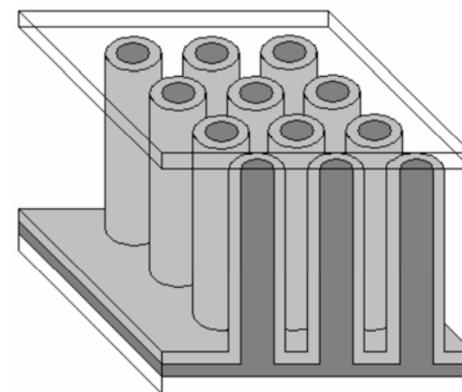
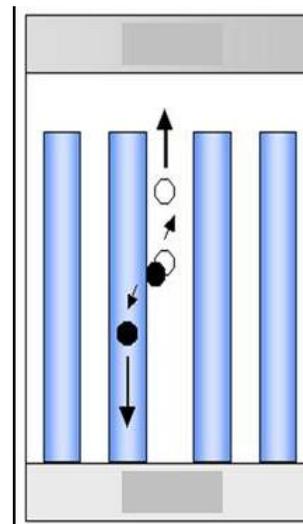
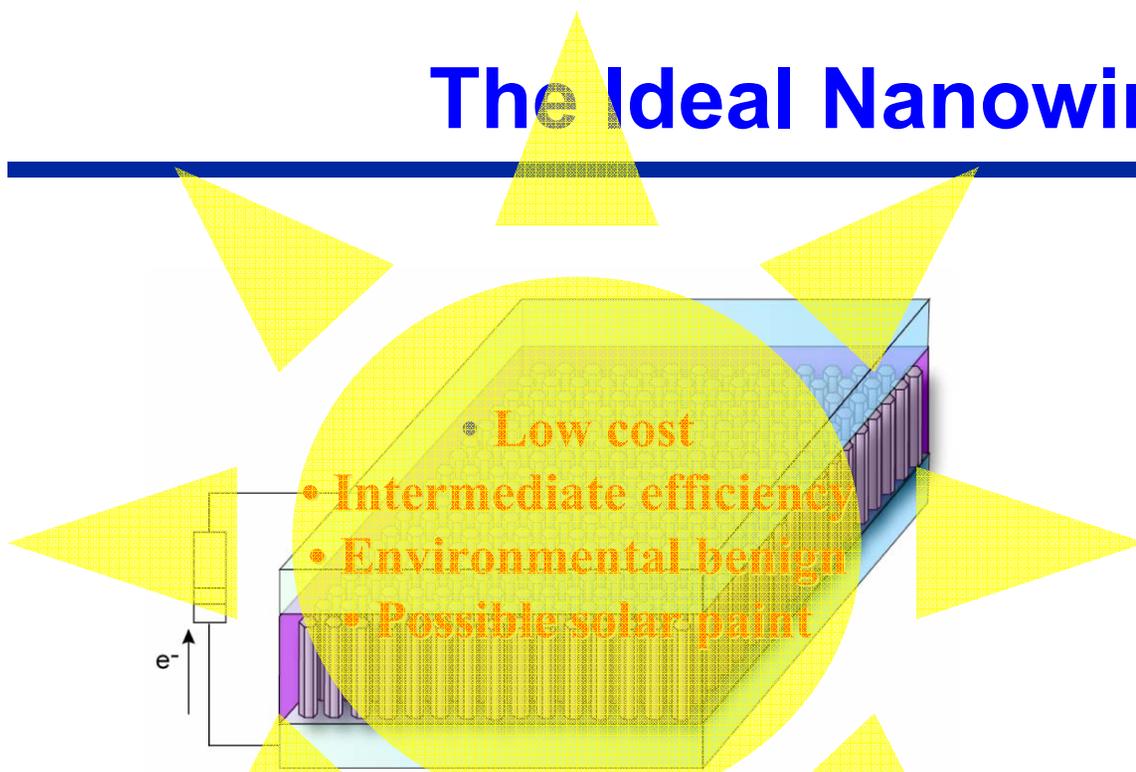
# Nanowire-polymer Composite Film



**Aligned wires**  
Inter-wire spacing is 10-50 nm  
 $2L_D$  for P3HT  $\sim$  20 nm  
Thickness 200-300 nm



# The Ideal Nanowire Cell



- **Fully interdigitated donor-acceptor interface**
- **Acceptor wire array: high density, smaller band gap**
- **Donor: polymer/nanoparticles, maximize absorption**
- **Interface engineering: reduce recombination.**
- **Applicable to DSC, hybrid, and conventional semiconductor cells.**

*N. Lewis*

# Acknowledgement



**Dr. Matt Law**  
**Lori Geene**  
**Dwaud Tan**



## Funding

**DOE**

**ITRI**

***Materials Sciences Division***